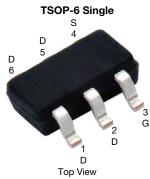
SQ3493EV

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Vishay Siliconix

Automotive P-Channel 20 V (D-S) 175 °C MOSFET



Marking Code: 9D

PRODUCT SUMMARY					
V _{DS} (V)	-20				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.021				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -2.5 V$	0.032				
I _D (A)	-8				
Configuration	Single				
Package	TSOP-6				

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified ^c
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



HALOGEN

FREE

(1, 2, 5, 6) D (3) G (4) S

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C :	= 25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-20	v
Gate-source voltage		V _{GS}	± 12	v
Continuous drain current	T _C = 25 °C	I-	-8	
Continuous drain current	T _C = 125 °C	I _D	-7	
Continuous source current (diode conduction)		I _S	-4.5	А
Pulsed drain current ^a		I _{DM}	-32	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-17	
Single pulse avalanche energy		E _{AS}	14.4	mJ
Maximum power dissipation ^a	T _C = 25 °C	PD	5	W
	T _C = 125 °C	۳D	1.67	vv
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount ^b	R _{thJA}	110	°C/W		
Junction-to-foot (drain)		R _{thJF}	30	0/10		

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)

c. Parametric verification ongoing

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SPECIFICATIONS (T _C = 25 °C		1				1	
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static		-1			T	T	
Drain-source breakdown voltage	V _{DS}	V _{GS}	$V_{GS} = 0, I_D = -250 \ \mu A$		-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V_{GS} , I_D = -250 μ A	-0.6	-1	-1.4	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 12 V$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -20 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = -20 V, T _J = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V_{DS} = -20 V, T_J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V_{GS} = -4.5 V	$V_{DS} \le -5 V$	-15	-	-	Α
		$V_{GS} = -4.5 V$	I _D = -5 A	-	0.016	0.021	Ω
Drain aquiras an atata registance à	В	$V_{GS} = -4.5 V$	$I_D = -5 \text{ A}, \text{ T}_J = 125 \ ^\circ\text{C}$	-	-	0.034	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 V$	I _D = -5 A, T _J = 175 °C	-	-	0.034	
		V _{GS} = -2.5 V	I _D = -4 A	-	0.026	0.032	
Forward transconductance ^a		V _{DS} =	V _{DS} = -10 V, I _D = -5.6 A		24	-	S
Dynamic ^b					-		
Input capacitance	C _{iss}		V V _{DS} = -10 V, f = 1 MHz	-	2354	3300	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	298	420	
Reverse transfer capacitance	C _{rss}			-	290	405	
Total gate charge ^c	Qg			-	22.7	34	
Gate-source charge ^c	Q _{gs}	V _{GS} = -4.5 V	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -7.9 \text{ A}$	-	4.5	-	nC
Gate-drain charge ^c	Q _{gd}			-	6.4	-	
Gate resistance	R _g		f = 1 MHz		5.9	9.4	Ω
Turn-on delay time ^c	t _{d(on)}			-	18	25	
Rise time ^c	t _r		$V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 1.27 \Omega$		41	58	- ns
Turn-off delay time ^c	t _{d(off)}	$I_D \cong$ -7.9 A, V_{GEN} = -4.5 V, R_g = 1 Ω		-	54	76	
Fall time ^c	t _f			-	51	71	
Source-Drain Diode Ratings and Char	racteristics ^b	·					
Pulsed current ^a	I _{SM}			-	-	-32	Α
Forward voltage	V _{SD}	I _F =	-	-0.8	-1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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T_C = 25 °C

T_C = 125 °C

20

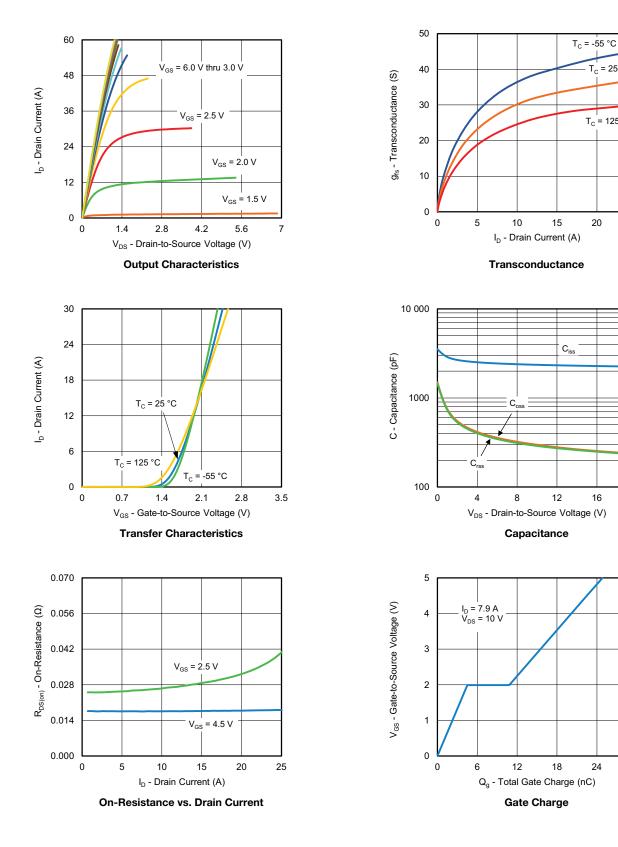
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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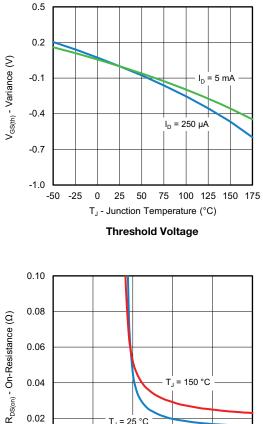
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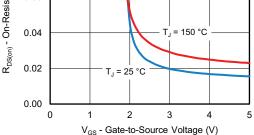
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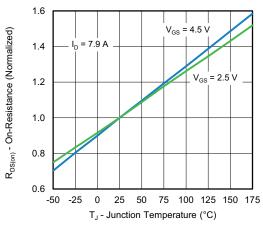
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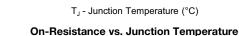
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





On-Resistance vs. Gate-to-Source Voltage





Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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10 I_s - Source Current (A) T_J = 150 °C 1 T_J = 25 °C 0.1 0.01 0 0.3 0.9 1.2 1.5 0.6 V_{SD} - Source-to-Drain Voltage (V) Source Drain Diode Forward Voltage 30 V_{DS} - Drain-to-Source Voltage (V) 29 m

100

28

27

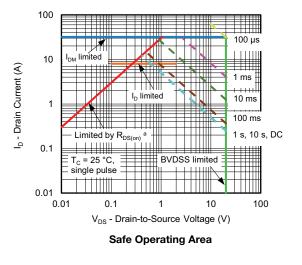
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-50 -25 0 25 50 75

T_J - Junction Temperature (°C) Drain Source Breakdown vs. Junction Temperature

100 125 150 175

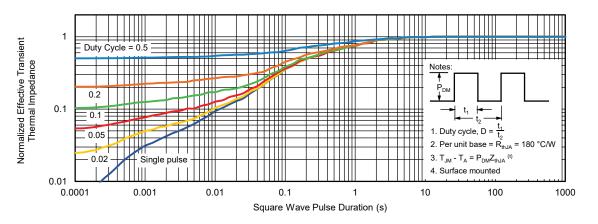




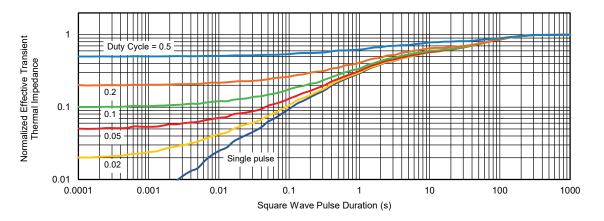
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77089.

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Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁		0.60 Ref 0.024			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom				7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Application Note 826

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RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)

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